

Reconfigurable organic ambipolar optoelectronic synaptic transistor for information security access

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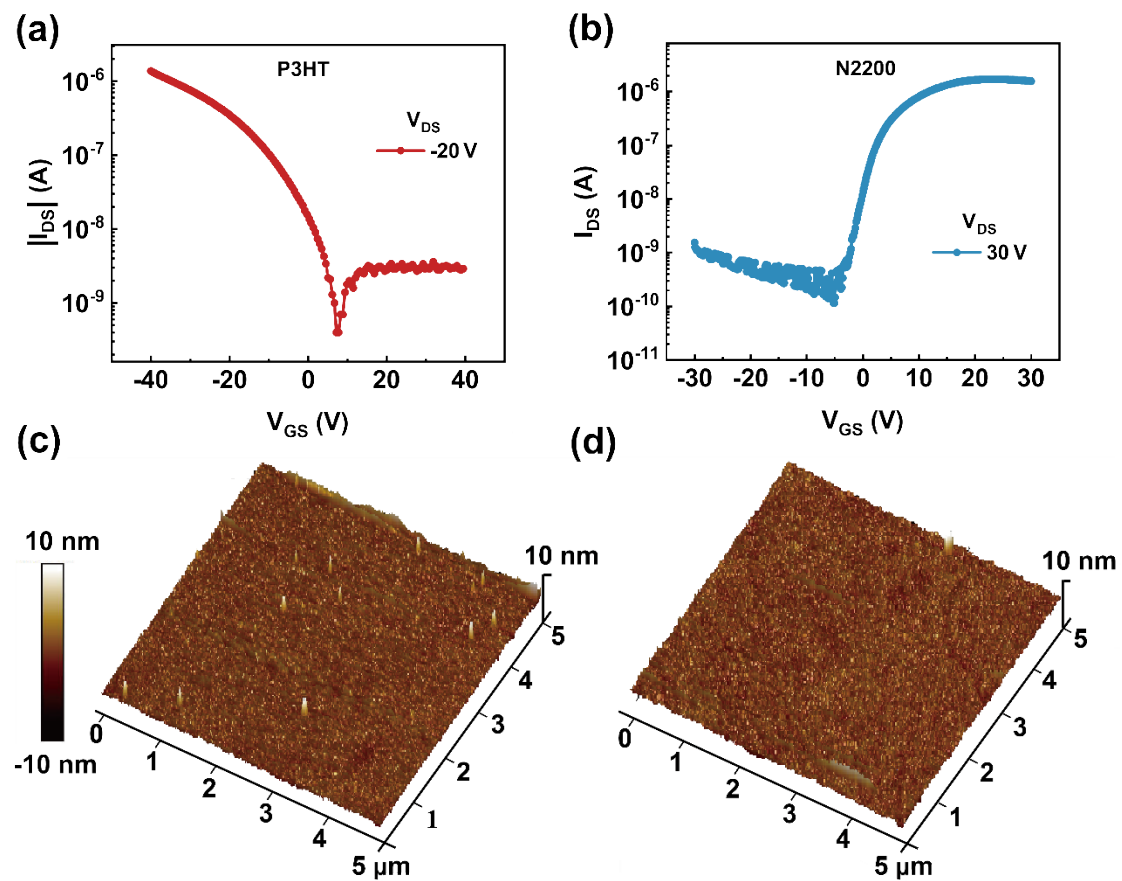
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Supplementary Fig. 1. (a and b) Transfer curves of P3HT (a) and N2200 (b) based transistor. (c and d) AFM images of pure P3HT (c) and (d) N2200 films.